



PATENT APPLICATION
Do. No. 9898-188

2811

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Mun-Mo JEONG

Serial No. 10/003,386

Examiner: Gebremariam, Samuel A

Confirmation No. 5232

Filed: October 30, 2001

Group Art Unit: 2811

For: SEMICONDUCTOR DEVICE WITH CONTACTS HAVING UNIFORM
CONTACT RESISTANCE AND METHOD FOR MANUFACTURING THE
SAME

BOX NON FEE AMENDMENT
Assistant Commissioner for Patents,
Washington, D.C. 20231

Responsive to the Office Action dated August 14, 2002, enclosed is an amendment in the
above-identified application.

The fee has been calculated as shown below.

CLAIMS AS AMENDED					
For:	Number After Amendment	Previous Number	Extra	Rate	Additional Fee
Total Claims	25 ¹⁸	20	0	x \$18 =	\$450.00
Independent Claims	3 ²	3 ²	0	x \$84 =	\$0
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT					\$450.00

*greater of twenty (20) or number for which fee has been paid

**greater of three (3) or number for which fee has been paid

Respectfully submitted,

MARGER JOHNSON & McCOLLOM, P.C.



20575

PATENT TRADEMARK OFFICE

Joseph S. Makuch
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I HEREBY CERTIFY THAT THIS COR-
RESPONDENCE IS BEING DEPOSITED
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ASSISTANT COMMISSIONER FOR
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ASSISTANT COMMISSIONER FOR
TRADEMARKS, 2900 CRYSTAL DRIVE
ARLINGTON VA 22202-3513
ON 11-13-02



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Do. No. 9898-188

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BOX NON FEE AMENDMENT
Assistant Commissioner for Patents
Washington, D.C. 20231

RESPONSE TO OFFICE ACTION

Responsive to the Office Action, dated August 14, 2002, please amend the application
as follows.

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IN THE CLAIMS

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1. (Once amended) A method for manufacturing a semiconductor device comprising:
 - forming plural interconnection layers, each including a capping layer, the capping layer defining a contact resistance, and an etching stopper, on a semiconductor substrate;
 - forming an interlayer insulating layer overlying the plural interconnection layers;
 - forming first contact holes in the interlayer insulating layer, thereby exposing a surface of the etching stopper;
 - removing a portion of the etching stopper exposed by the first contact holes, thereby forming second contact holes, to leave the capping layers of the plural interconnection layers at substantially the same thickness such that the contact resistances of the plural interconnection layers are substantially uniform; and
 - forming a conductive layer within the second contact holes.